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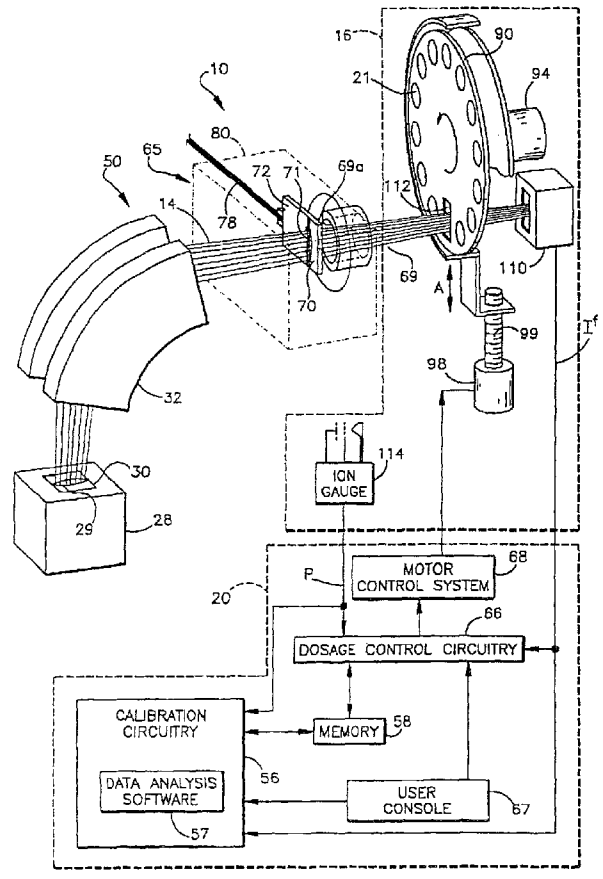
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(54) Title: METHOD AND SYSTEM FOR DETERMINING PRESSURE COMPENSATION FACTORS IN AN ION IMPLANTER



(57) Abstract: The invention provides a method and system for determining a pressure compensation factor for use in an ion implanter, which uses one or a small number of test workpieces (21). The method includes providing a test workpiece (21) in the ion implantation system (10), wherein the test workpiece (21) has at least one band region, assuming (302) a predicted pressure compensation factor (Kused), implanting (304) the at least one band region of the test workpiece (21) with an ion beam (14) using the ion implantation system (10) and the predicted pressure compensation factor (Kused) while measuring (306) ion beam current (Iimplanted) and a pressure (P) in the ion implantation system (10), measuring (308) a sheet resistance (Rs(measured)) associated with the implanted test workpiece (21), and determining (310) a pressure compensation factor (Kpredicted) according to the predicted pressure compensation factor (Kused), the measured sheet resistance (Rs(measured), the measured ion beam current (Iimplanted), and the measured pressure (P).

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